

NTMS4176P

Power MOSFET

-30 V, -9.6 A, P-Channel, SOIC-8

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- SOIC-8 Surface Mount Package Saves Board Space
- This is a Pb-Free Device

Applications

- Load Switches
- Notebook PC's
- Desktop PC's

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Rating		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	-30	V
Gate-to-Source Voltage		V_{GS}	± 25	V
Continuous Drain Current $R_{\theta JA}$ (Note 1)	$T_A = 25^\circ\text{C}$	I_D	-7.3	A
	$T_A = 70^\circ\text{C}$		-5.8	
Power Dissipation $R_{\theta JA}$ (Note 1)	$T_A = 25^\circ\text{C}$	P_D	1.44	W
Continuous Drain Current $R_{\theta JA}$ (Note 2)	$T_A = 25^\circ\text{C}$	I_D	-5.5	A
	$T_A = 70^\circ\text{C}$		-4.4	
Power Dissipation $R_{\theta JA}$ (Note 2)	$T_A = 25^\circ\text{C}$	P_D	0.81	W
Continuous Drain Current $R_{\theta JA} t < 10$ s (Note 1)	$T_A = 25^\circ\text{C}$	I_D	-9.6	A
	$T_A = 70^\circ\text{C}$		-7.7	
Power Dissipation $R_{\theta JA} t < 10$ s (Note 1)	$T_A = 25^\circ\text{C}$	P_D	2.5	W
Pulsed Drain Current	$T_A = 25^\circ\text{C}$, $t_p = 10 \mu\text{s}$	I_{DM}	-39	A
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Source Current (Body Diode)		I_S	-2.1	A
Single Pulse Drain-to-Source Avalanche Energy $T_J = 25^\circ\text{C}$, $V_{DD} = 30$ V, $V_{GS} = 10$ V, $I_L = 15$ A _{pk} , $L = 1.0$ mH, $R_G = 25 \Omega$		EAS	112.5	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using 1 inch sq pad size, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.

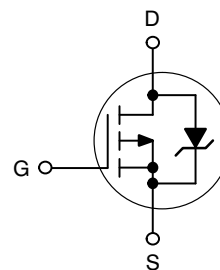


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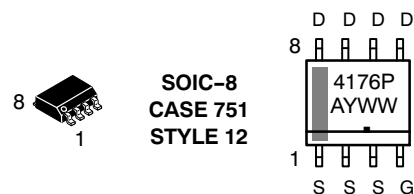
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ Max	I_D Max
-30 V	18 m Ω @ -10 V	-9.6 A
	30 m Ω @ -4.5 V	

P-Channel



MARKING DIAGRAM & PIN ASSIGNMENT



4176P = Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ■ = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NTMS4176PR2G	SOIC-8 (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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THERMAL RESISTANCE RATINGS

Rating	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	87	°C/W
Junction-to-Ambient – $t \leq 10$ s (Note 3)	$R_{\theta JA}$	50	
Junction-to-FOOT (Drain)	$R_{\theta JF}$	22	
Junction-to-Ambient – Steady State (Note 4)	$R_{\theta JA}$	154	

3. Surface-mounted on FR4 board using 1 inch sq pad size, 1 oz Cu.

4. Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)jk

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			29		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = -24\text{ V}$			-1.0	μA
					-5.0	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 25\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\ \mu\text{A}$	-1.5		-2.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			6.0		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -9.6\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -7.5\text{ A}$		14	18	m Ω
				23	30	
Forward Transconductance	g_{FS}	$V_{DS} = -1.5\text{ V}, I_D = -9.6\text{ A}$		21.5		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = -24\text{ V}$		1720		pF
Output Capacitance	C_{OSS}			370		
Reverse Transfer Capacitance	C_{RSS}			256		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5\text{ V}, V_{DS} = -15\text{ V}, I_D = -9.6\text{ A}$		17		nC
Threshold Gate Charge	$Q_{G(TH)}$			2.0		
Gate-to-Source Charge	Q_{GS}			6.0		
Gate-to-Drain Charge	Q_{GD}			8.4		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -10\text{ V}, V_{DS} = -15\text{ V}, I_D = -9.6\text{ A}$		32.6		nC
Gate Resistance	R_G			3.0	4.5	Ω

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -10\text{ V}, V_{DD} = -15\text{ V}, I_D = -1.0\text{ A}, R_G = 6.0\ \Omega$		15		ns
Rise Time	t_r			9.0		
Turn-Off Delay Time	$t_{d(OFF)}$			19.5		
Fall Time	t_f			42.5		

DRAIN-TO-SOURCE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_D = -2.1\text{ A}$	$T_J = 25^\circ\text{C}$		-0.75	-1.0	V
			$T_J = 125^\circ\text{C}$		0.59		ns
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, d_{IS}/d_t = 100\text{ A}/\mu\text{s}, I_S = -2.1\text{ A}$			32.4		
Charge Time	T_a				14		
Discharge Time	T_b				18.4		
Reverse Recovery Time	Q_{RR}				23		

5. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

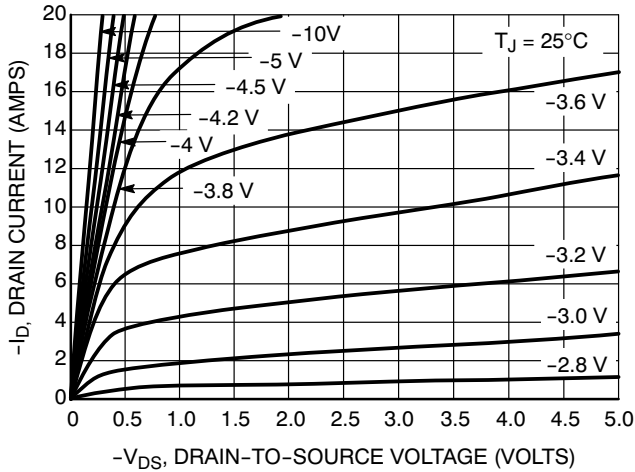


Figure 1. On-Region Characteristics

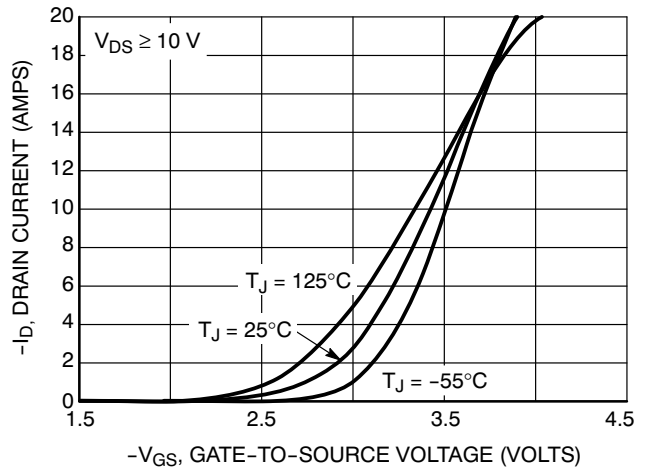


Figure 2. Transfer Characteristics

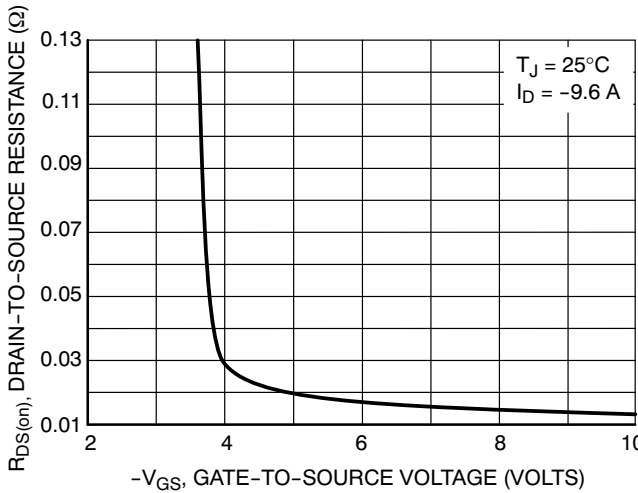


Figure 3. On-Resistance vs. Gate-to-Source Voltage

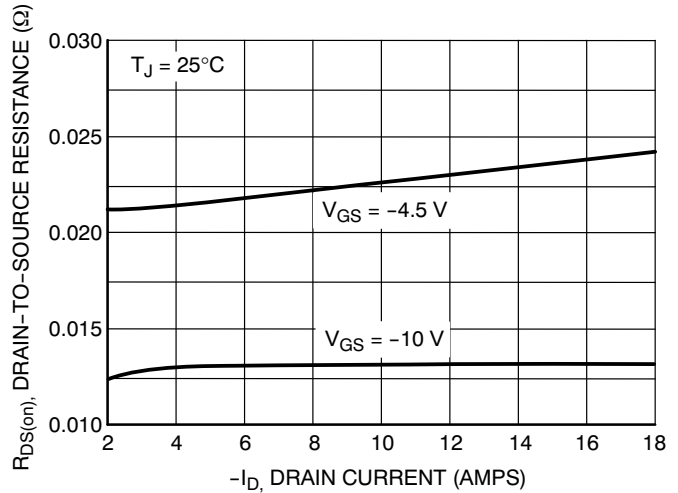


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

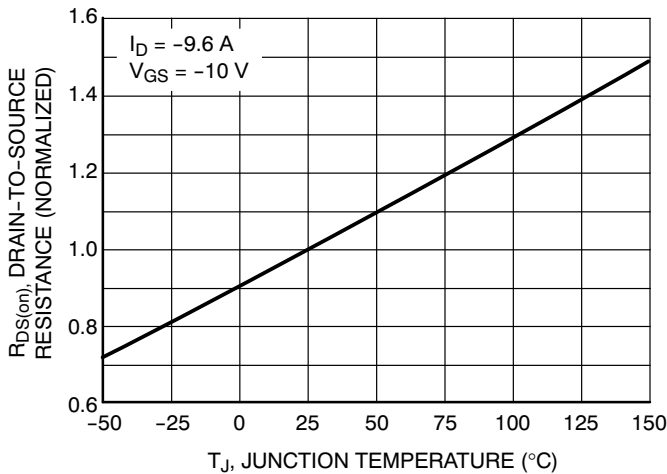


Figure 5. On-Resistance Variation with Temperature

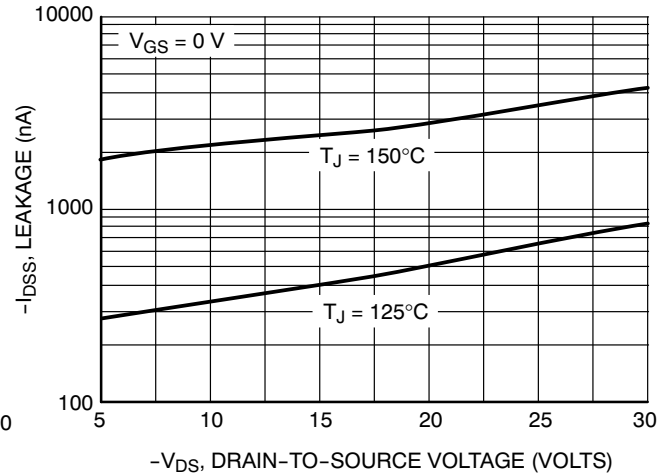


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL PERFORMANCE CURVES

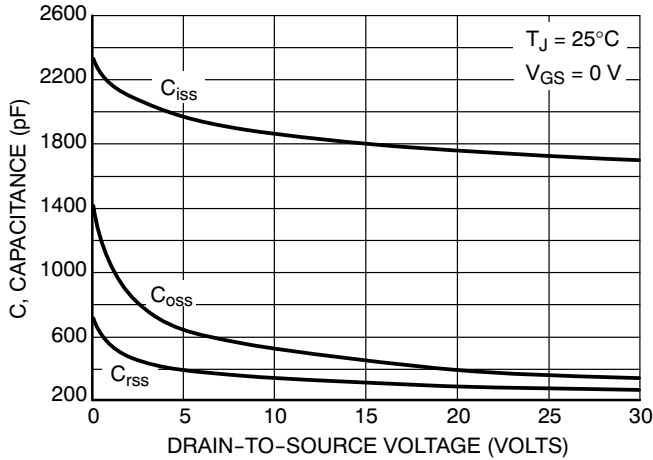


Figure 7. Capacitance Variation

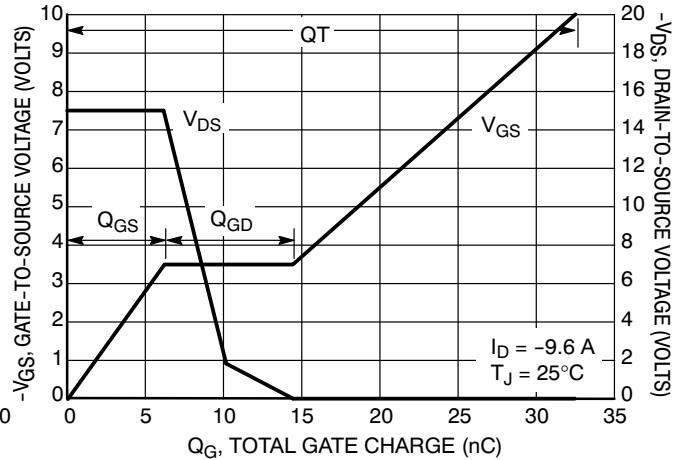


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

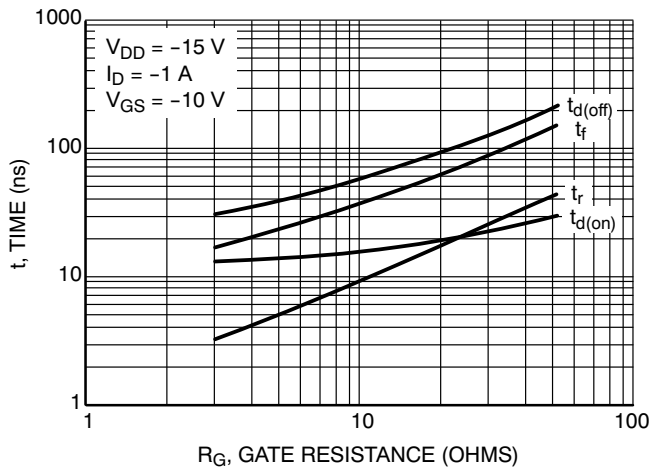


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

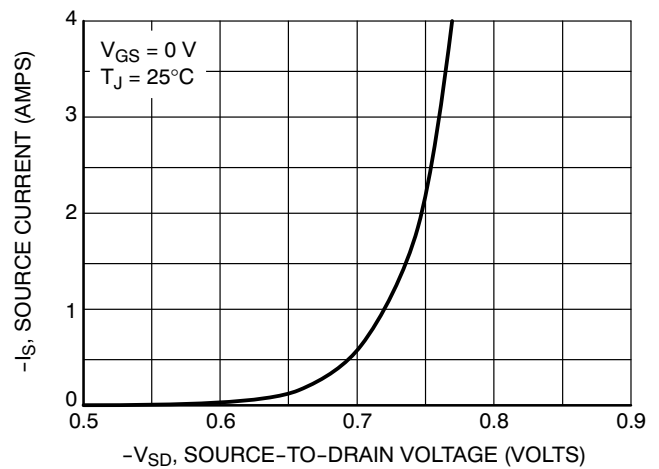


Figure 10. Diode Forward Voltage vs. Current

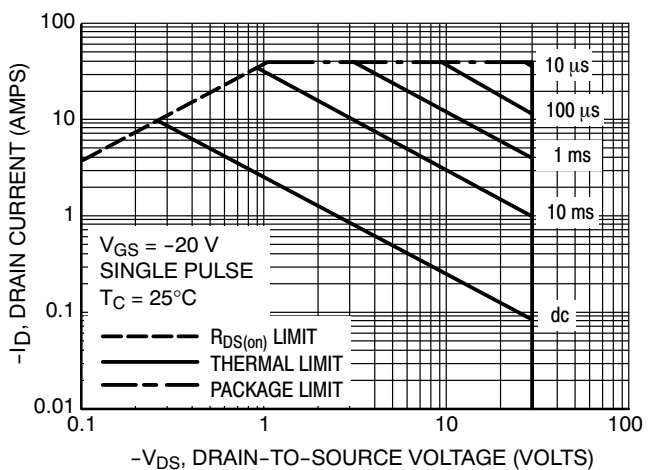


Figure 11. Maximum Rated Forward Biased Safe Operating Area

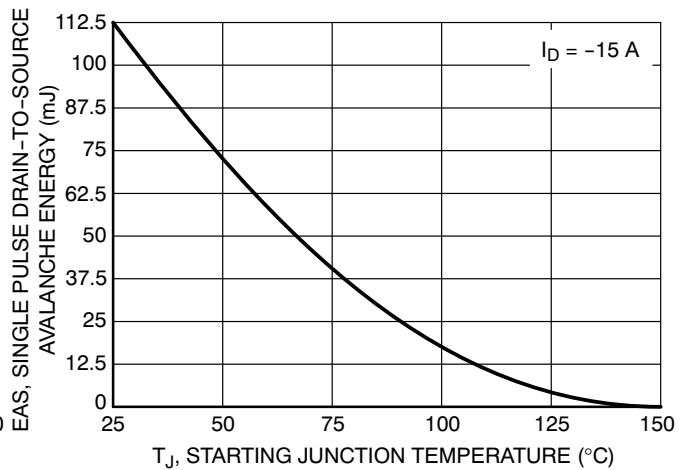
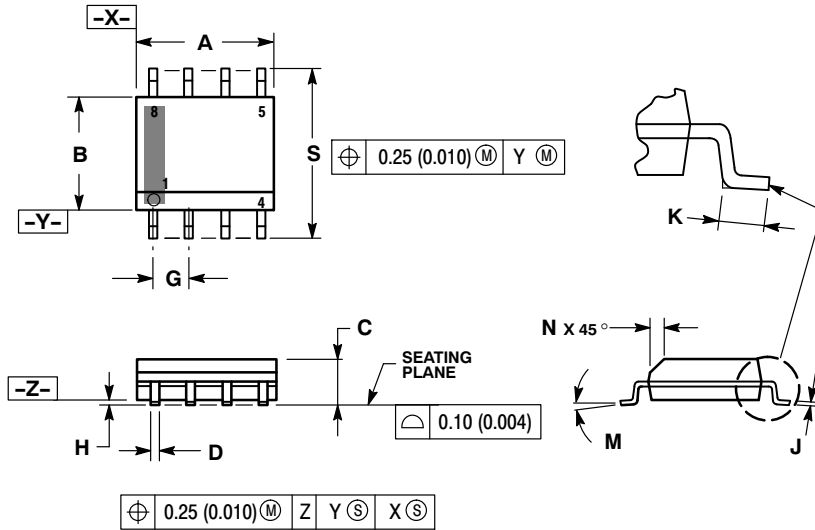


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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PACKAGE DIMENSIONS

SOIC-8 NB CASE 751-07 ISSUE AJ



NOTES:

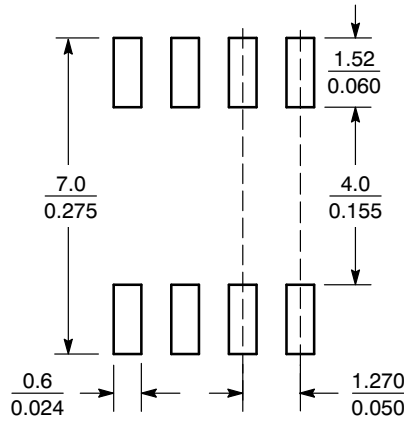
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

STYLE 12:

- PIN 1. SOURCE
- SOURCE
- SOURCE
- GATE
- DRAIN
- DRAIN
- DRAIN
- DRAIN

SOLDERING FOOTPRINT*



SCALE 6:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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